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Amplifier Applications

• **G**

PE =33 dB (Typical)at f =45 MH

- Suffix "C"means Center Collector (. Emitter 2. Collector 3. Base)
- Non Suffix "C"means Side Collector (1. Emitter 2. Base 3. Collector)

Ordering Information

Part Number	Top Mark	Package	Packing Method
KSC388CYTA	C388	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{\sf CBO}$	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current	50	mA
T_J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to 150	°C

Thermal Characteristics(1)

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Value	Unit
В	Power Dissipation	300	mW
P _D	Derate Above 25°C	2.4	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	416	°C/W

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	30			V
BV _{CEO}	$ \begin{array}{ccc} \text{BV}_{\text{CEO}} & \text{Collector-Emitter Breakdown Voltage} & \text{I}_{\text{C}} = 5 \text{ mA}, \text{I}_{\text{B}} = 0 \\ \\ \text{I}_{\text{CBO}} & \text{Collector Cut-Off Current} & \text{V}_{\text{CB}} = 30 \text{ V}, \text{I}_{\text{E}} = 0 \\ \end{array} $		25			V
I _{CBO}					0.1	μΑ
I _{EBO}	I_{EBO} Emitter Cut-Off Current $V_{EB} = 3 \text{ V}, I_{C} = 0$				0.1	μΑ
h _{FE}	h_{FE} DC Current Gain $V_{CE} = 12.5 \text{ V}, I_C = 12.5 \text{ mA}$		20		200	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	on Voltage $I_C = 15 \text{ mA}, I_B = 1.5 \text{ mA}$			0.2	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 15 \text{ mA}, I_B = 1.5 \text{ mA}$			1.5	V
C _{ob}	Output Capacitance	Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			2	pF
C _{c·rbb}	Collector-Base Time Constant	$V_{CB} = 10 \text{ V, } I_{C} = 1 \text{ mA,}$ f = 30 MHz			25	ps
f _T	Current Gain Bandwidth Product	$V_{CE} = 12.5 \text{ V}, I_{C} = 12.5 \text{ mA}$	300			MHz
$V_{CE} = 12.5 \text{ V}, I_{C} = 12.5 \text{ W}$ F = 45 MHz		$V_{CE} = 12.5 \text{ V}, I_{C} = 12.5 \text{ mA},$ f = 45 MHz	28	33	36	dB

Typical Performance Characteristics

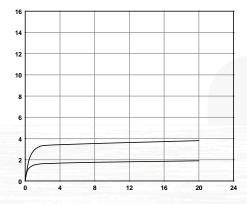


Figure 1. Static Characteristic

Figure 2. DC Current Gain

Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

Figure 4. Base-Emitter On Voltage

Figure 5. Collector Input Capacitance Collector Output Capacitance

Figure 6. Current Gain Bandwidth Product

